G. Device & Process Modeling, Simulation and Reliability 분과

2021년 1월 27일(수), 09:00–10:30 / 채널 D

[WD1-G] DTCO and Memory Devices

좌장: 서지웅 팀장 (SK하이닉스), 이재우 교수 (고려대학교)

WD1-G-1 **09:00-09:30**	[초청] **Toward the Material-Device-circuit Co-design of the Oxide Semiconductor-based Artificial Intelligence: from Transistor, Memory, and Sensor to Modeling, Simulation, and Reliability** Dae Hwan Kim *School of Electrical Engineering, Kookmin University*
WD1-G-2 **09:30-09:45**	**Design Optimization of FeFET-based TCAM Cell Using Compact Model Combining Ferroelectric Switching and Conventional MOSFETs** Boram Yi[1], Tae Woo Oh[2], Seong-Ook Jung[2], Sanghun Jeon[3], and Ji-Woon Yang[1] *[1]Department of Electronic and Information Engineering, Korea University, [2]School of Electrical and Electronic Enginnering, Yonsei University, [3]School of Electrical Engineering, KAIST*
WD1-G-3 **09:45-10:00**	**Novel Trap Profiling in Nitride Layer Using Space Program for 3-D NAND Flash Memory** Jounghun Park, GilSang Yoon, Jaeseok Jin, DongHyun Go, and Jeong-Soo Lee *Department of Electrical Engineering, POSTECH*
WD1-G-4 **10:00-10:15**	**A Finite Element Simulation of a Full Switching Cycle in Resistive Memory** Dongmyung Jung and Yongwoo Kwon *Department of Materials Science and Engineering, Hongik University*
WD1-G-5 **10:15-10:30**	**Investigation of Trap Profiles of Tunneling and Blocking Layers after P/E Cycling Stress in 3-D VNAND Flash Memory** Gilsang Yoon, DongHyun Go, Jaeseok Jin, Jounghun Park, and Jeong-Soo Lee *Department of Electrical Engineering, POSTECH*